

Supplementary material

Graphene Nanogap Interdigitated Asymmetric Electrodes for Photodetection

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Table S1. Power of light used in the photoresponsivity measurement.

λ/nm	400	500	600	700	800	900
Power density / W m^{-2}	0.47	1.09	1.42	1.32	1.16	1.47

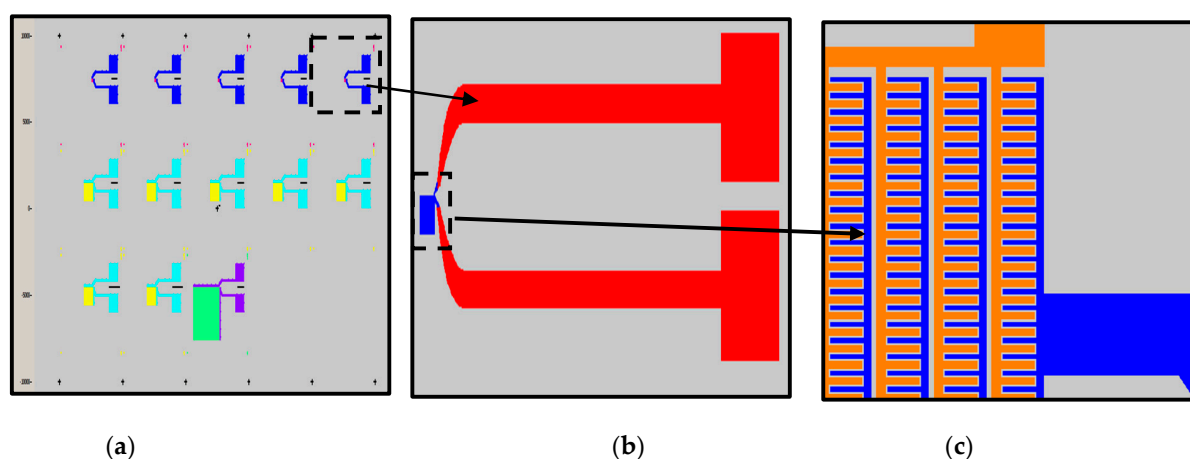
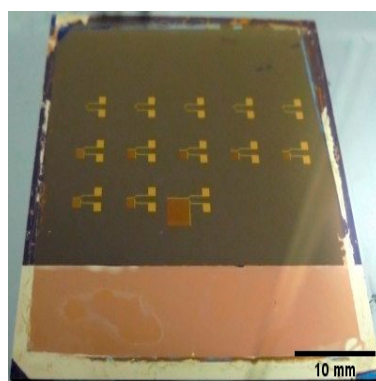


Figure S1. Illustration of the devices' design using LibreCAD software, including (a) the overview of all devices, (b) zoom on 100 μm device, and (c) zoom on the IDEs (Au-Pt).



(a)



(b)

Figure S2. Optical images of devices (a) before and (b) after ion milling.

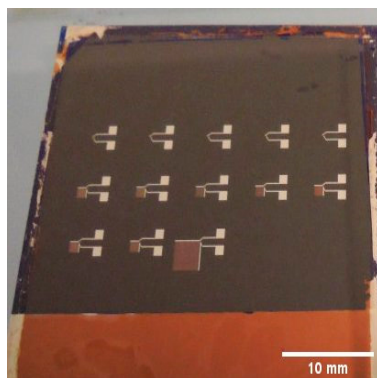
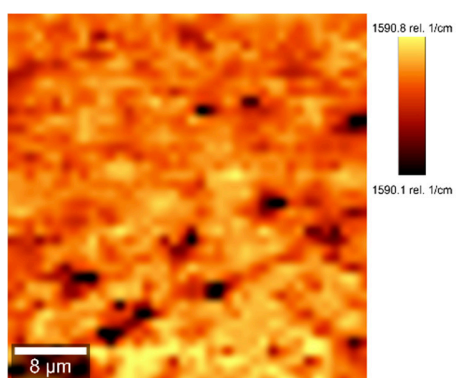
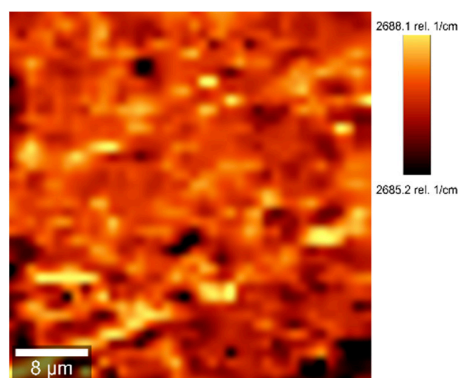


Figure S3. Optical images of devices.



(a)



(b)

Figure S4. Raman mapping of (a) the G and (b) 2D bands positions.